Magnetoresistance in 2D Electrons on Liquid Helium: Many-Electron versus Single-Electron Kinetics

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The magnetoresistance ρ_{xx} of two-dimensional electrons, density *n*, on liquid helium was measured up to the quantum limit, near 1 K where the scattering is due to ⁴He vapor atoms. Temperature- and density-dependent positive magnetoresistance was observed. Many-electron theory is presented that "restores" the Drude formalism for $\hbar \omega_p \ll kT \ll e^2 n^{1/2}/\epsilon_0 \ [\omega_p = (e^2 n^{3/2}/2\epsilon_0 m)^{1/2}$ is the plasma frequency] for classically strong magnetic fields, and shows large magnetoresistance in higher fields, in agreement with the data. The crossover to single-electron kinetics at the highest fields is discussed.

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Electron-electron interactions produce many interesting phenomena in two-dimensional electron systems (2DES) [1], such as the classical electron solid on liquid helium [2], the fractional quantum Hall effect [3], and the proposed magnetically induced Wigner solid in semiconductors [4]. However, there should also be manyelectron dynamic effects which are not immediately related to long-range order. This Letter discusses the influence of these effects on the magnetoresistivity $\rho_{xx}(B)$ of a nondegenerate 2D electron gas (2DEG), density n, on liquid helium in a perpendicular magnetic field B. For instance, why should the single-electron approximation apply at all, since the electron-electron energy $e^{i2n} \tilde{l}/2/\epsilon_0 \gg kT$, the thermal energy, at low temperatures T in this system? Nevertheless the classical Drude model based on elastic (or quasielastic) scattering of independent electrons has been demonstrated to be in good agreement with the experimental data for B = 0. In a field it predicts a resistivity $\rho_{xx}(B) = \rho_0 = 1/ne\mu_0$ where μ_0 is the zero-field mobility but is commonly recognized to fail for classically strong magnetic fields, $\mu_0 B > 1$, where the density of states is concentrated into a set of discrete Landau levels whose spacing exceeds their width. In this case large magnetoresistance would be expected to arise for $B > 1/\mu_0$. The mobility μ_0 is strongly temperature dependent, increasing from 2 m²/Vs at 2 K (where electrons are scattered by ⁴He atoms) to over $10^3 \text{ m}^2/\text{Vs}$ below 0.5 K where ripplon scattering dominates. Above 1.5 K positive magnetoresistance for $B > 1/\mu_0$ has indeed been observed experimentally and is described [5-8] by a single-particle self-consistent Born approximation (SCBA). However, for lower temperatures (and higher mobilities) there is no large magnetoresistance for $B \sim 1/\mu_0$, and we have previously shown that manyelectron effects are important in quantizing magnetic fields in electron-ripplon scattering below 1 K [9-11]. We now present new measurements and theory for $\rho_{xx}(B)$ near 1 K, in fields up to the quantum limit $\hbar \omega_c / kT \gg 1$, where the scattering is dominated by ⁴He vapor atoms whose density increases exponentially with T

and which act as short-range scattering centers, ideal for comparison with theoretical models. The data indicate the many-electron character of the kinetics and the theory resolves the controversy about the applicability of the Drude model to many-electron systems.

We measured the magnetoresistance of a 2DEG on superfluid helium using the Sommer-Tanner technique [12] with coplanar electrodes (see Fig. 1) in a rectangular geometry 120 μ m below the electron sheet. An ac voltage V_0 at a frequency $f(=\omega/2\pi)$ between 0.27 and 5 kHz was applied to electrode A and the ac current I to electrode D was measured. For a perfectly conducting electron sheet at B=0 the phase of the capacitively coupled current I is $\pi/2$ with respect to V_0 . The phase shift $\phi(B)$ away from $\pi/2$ was measured as a function of B for a range of electron densities, for temperatures 0.9 < T< 1.3 K. The data cover a wide range of $\mu_0 B$ values and



FIG. 1. The normalized resistivity $\rho^*(B)$ vs B for $n = 0.6 \times 10^{12} \text{ m}^{-2}$, T = 1.003 K. The lines show the theory for independent electrons, ρ_s^* (line a_1), the classical many-electron theory ρ_{mc}^* , Eq. (5) (line b_1), the quantum many-electron theory ρ_{mq}^* , Eq. (6) (line c_1), and the total resistivity, ρ_t^* (line d_1). The onset field B_0 and the quantum limit, $\hbar \omega_c/kT = 1$ at B_q , are marked. (Inset: electrode geometry.)

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FIG. 2. The density dependence of $\rho^*(B)$ vs B for n=0.6(∇ , data set 1) and 2.1 (\Box , data set 2) ×10¹² m⁻² at T=1.003K. The *a* and *d* lines show the theory for independent electrons, ρ_s^* , and the total resistivity, ρ_t^* , from Eq. (7), respectively, for data sets 1 and 2.

extend into the quantum limit $\hbar \omega_c/kT \gg 1$. The electrons were produced by a glow discharge and held in place by dc voltages on the electrodes, a surrounding guard ring and a top plate 1.93 mm above the helium surface. The electron density was determined from the linear Hall voltage $V_H \propto B/ne$ as measured between electrodes *B* and *C* and calibrated using the transition to the 2D electron solid phase at $T_m = 0.216 \times 10^{-6} n^{1/2}$ K [1,13,14].

The phase shift $\phi(B)$ in a magnetic field for rectangular electrodes is given by [15,16]

$$\phi(B) = K\omega\rho_{xx} [1 + (a\rho_{xy}/\rho_{xx})^2]$$

= $\phi_0 \rho^* [1 + (a\mu_0 B/\rho^*)^2],$ (1)

where K and a (=0.225 in this case) depend on the electrode geometry. The second expression, for the normalized resistivity $\rho^* = \rho_{xx}(B)/\rho_0$, is obtained by using the Hall resistance $\rho_{xy} = B/ne$ as confirmed experimentally [5,7] in agreement with theoretical arguments [5,17]. Hence we can obtain $\rho^*(B,T)$ from the measured $\phi(B)$. In very low fields, where $\rho^* \approx 1$, the initial slope of $\phi(B)/\phi_0$ is proportional to $(\mu_0 B)^2$ and directly gives the zero-field mobility. Typical values of μ_0 were 26, 34, 52, 92, and 140 m²/Vs for T = 1.252, 1.215, 1.082, 1.003, and 0.924 K, respectively, in agreement with other experiments [18] and single-electron calculations in zero field [19].

Positive magnetoresistance was observed for all densities and temperatures investigated, cf. Figs. 1 to 3. The main features of the data are the same. In low fields the normalized resistivity ρ^* is almost independent of field, though it increases slowly and quadratically with field. At higher fields the resistivity increases rapidly and the value of ρ^* at a given field increases with decreasing density (Fig. 2) and temperature (Fig. 3). The data sets



FIG. 3. The temperature dependence of $\rho^*(B)$ vs B for $n=2.1\times10^{12}$ m⁻² at 1.003 K (\Box , data set 2) and at 1.215 K (\diamond , data set 3). The a and d lines show the theory for independent electrons, ρ_s^* , and the total resistivity, ρ_t^* , from Eq. (7), respectively, for data sets 2 and 3.

shown were taken at 956 Hz; ρ^* was independent of frequency below 5 kHz. At much higher fields, ≈ 60 T at 1 kHz, an edge magnetoplasmon resonance should be observed [20].

A remarkable feature of the observed magnetoresistance is that it is relatively small for classically strong magnetic fields: $\rho^* < 1.1$ even for B = 0.4 T where $\mu_0 B > 10$ and hence the Landau-level spacing is more than an order of magnitude larger than the level width as given by \hbar/τ_0 (τ_0 is the momentum relaxation time for B=0). In the conventional single-electron theory based on the SCBA the width of the levels \hbar/τ_B is due to electron collisions with ⁴He vapor atoms and, since the density of states increases due to the "squeezing" of the energy spectrum into Landau levels, $\tau_B^{-1} = (2\mu_0 B/\pi)^{1/2} \tau_0^{-1}$ for $\mu_0 B \gg 1$ and increases sharply with B [6,17]. In the classical limit, $\hbar \omega_c/kT \ll 1$, this leads to $\rho_s^* \approx (\mu_0 B)^{1/2}$ while in the quantum limit, $\hbar \omega_c/kT \gg 1$, $\rho_s^* \approx (\mu_0 B)^{1/2}$ $\times (\hbar \omega_c / kT)$. The full theoretical expression for ρ_s^* using the SCBA for a nondegenerate 2DES has been given by van der Heijden et al. [6] and is shown (line a) in the figures. In each case ρ_s^* lies above the data and shows a stronger field dependence. It is this striking observation which indicates the importance of many-electron effects and is the subject of this paper. Moreover, ρ^* displays a density dependence that also indicates the influence of many-electron effects.

The onset of many-electron magnetoresistance and the agreement between the single-electron theory and experiment for B = 0 can be understood since the result of the strong electron-electron coupling for $e^2 n^{1/2} / \epsilon_0 \gg kT$ is that an electron is driven by a fluctuational (and fluctuating) electric field **E** from the other electrons. If this field is weak so that the change of kinetic energy over a thermal wavelength $\delta \varepsilon = eE\lambda_T \ll kT [\lambda_T = \hbar/(2mkT)^{1/2}; E = \langle \mathbf{E}^2 \rangle^{1/2}]$, the electron motion is semiclassical [21]. A

quasielastic collision with a short-range scatterer is then not influenced by many-electron effects (provided E does not change over the collision time \hbar/kT) and the singleparticle approximation holds for B=0.

For $\mu_0 B \gg 1$ the fluctuational field **E** can dramatically change the magnetotransport, compared to the singleelectron theory, as the energy spectrum of an electron in crossed **B** and **E** fields is continuous (not discrete as for

$$\rho^* \equiv \rho_{m}^* = (\chi_T/\lambda)^2 (\tau_0/\tau_B); \quad \tau_B^{-1} = \frac{1}{2} \lambda^2 \hbar^{-2} \sum_{\mathbf{q}} q^2 \overline{|V_q|^2} \xi(q) ,$$

$$\xi(\mathbf{q}) = \int_{-\infty}^{\infty} dt \, \xi(\mathbf{q}, t); \quad \xi(\mathbf{q}, t) = \langle \exp[i\mathbf{q} \cdot \mathbf{r}_j(t)] \exp[-i\mathbf{q} \cdot \mathbf{r}_j(0)] \rangle .$$

Here, $|V_{\mathbf{q}}|^2$ is the mean squared Fourier component of the random quasistationary scattering field, \mathbf{r}_j is the position vector of the *j*th electron, and λ is a characteristic wavelength of an electron; $\lambda = \lambda_T$ for $\hbar \omega_c \ll kT$ and $\lambda = l = (\hbar/eB)^{1/2}$, the magnetic length, for $\hbar \omega_c \gg kT$.

The electron-electron coupling determines the kinetics of an individual electron and thus the value of the correlator $\xi(\mathbf{q},t)$. In other words, Eq. (2) gives the magnetoconductivity due to the momentum transfer from the "electron community" via the scattering of individual electrons. The scattering rate for a nondegenerate 2DES has been given previously in the extreme quantum limit $\hbar\omega_c \gg kT$ [23,24]. Here we present a theory of magnetoresistance for arbitrary magnetic fields.

In the single-electron approximation at $B=0, \xi(q)$ = $(2\pi m/kTq^2)^{1/2} \exp(-\hbar^2 q^2/8mkT)$, whereas for finite B the integral in Eq. (2) diverges as an electron moves along a closed loop in classical terms. This is no longer true if the electron is also driven by an electric field from the other electrons. The value of $\xi(q)$ and the physics of the scattering depend on the value of the parameter $\eta = \omega_c (2mkT)^{1/2}/eE$ which gives the ratio of the cyclotron radius $R_c = (2kT/m\omega_c^2)^{1/2}$ to the shift of the orbit in the crossed **E** and **B** fields over the time ω_c^{-1} , or in quantum terms, the ratio of $\hbar\omega_c$ to the uncertainty $eE\lambda_T$ in the kinetic energy of an electron. For $\eta \ll 1$ (small fields) the Landau levels are smeared out and the scattering is basically as for B = 0. The evaluation of $\xi(q)$ in this limit requires the solution of the equations of motion for small times $\sim \hbar/kT$ with the magnetic field and the electron-electron interaction as perturbations. This leads to a small quadratic magnetoresistance

$$\rho_{mc}^* = 1 + (5/96)(\hbar \omega_c / kT)^2.$$
(3)

The *E*-dependent correction $[-\hbar^2 e^2 E^2/48m(kT)^3]$ to τ_B^{-1} is additive, and therefore does not enter ρ^* in this regime.

A different situation arises for $\eta \gg 1$ (still $\hbar \omega_c/kT \ll 1$) when, before the many-electron field drives it away, an electron performs several rotations about a scatterer, increasing the probability of scattering. The correlator $\xi(q)$ was evaluated by the steepest descent method, with saddle points at $2\pi s/\omega_c - i\hbar/2kT$. The many-electron E=0), and an electron can be scattered quasielastically by a short-range scatterer (a He atom). Since only one electron is immediately involved in a collision (neglecting momentum transfers of order $\hbar n^{1/2}$), the expression for magnetoconductivity to the lowest order in the coupling is the same as the Drude theory [22], with the only (but important) difference that the electron-electron interaction influences the motion of an electron in the course of a collision and hence

field causes drift of the cyclotron orbit by (E/B)t, with $t = 2\pi s/\omega_c$, and therefore

$$\xi(q) \approx \left(\frac{2\pi m}{kTq^2}\right)^{1/2} \sum_{s} \exp\left(\frac{-\hbar^2 q^2}{8mkT}\right) \\ \times \left\langle \exp\left(\frac{i2\pi se}{m\omega_c^2} \mathbf{E} \cdot \mathbf{q}\right) \right\rangle.$$
(4)

The values of the integer s which contribute to the sum are limited to $|s| \approx \zeta = \hbar \omega_c / eER_c = \eta(\hbar \omega_c / 2kT)$. The magnetoresistance increases rapidly for $B > B_0$ ($\zeta = 1$ for $B = B_0$). The onset field B_0 is the field above which the electron drift over the time ω_c^{-1} is less than the thermal wavelength λ_T . If the distribution of the many-electron field is Gaussian and the electrons are scattered by vapor atoms then Eqs. (2)-(4) give

$$\rho_{mc}^{*} = \sum_{s=-\infty}^{\infty} \left[1 + 4\pi^{2} s^{2} (B_{0}/B)^{4} \right]^{-3/2}.$$
 (5)

The onset field B_0 depends on the fluctuational electric field which can be estimated by assuming short-range order in the electron system (which seems reasonable for $e^2n^{1/2}/\varepsilon_0 \gg kT$) by equating kT to the energy $e^2E^2/m\omega_p^2$ of electron vibrations in the field of other electrons at a characteristic 2D plasma frequency $\omega_p = (e^2n^{3/2}/2\varepsilon_0m)^{1/2}$ [23]; one arrives at $E \approx 0.84(kTn^{3/2}/\varepsilon_0)^{1/2}$ [24], $\eta \sim \omega_c/\omega_p$ and $B_0 = 1.66 \times 10^{-5}n^{3/8}T^{1/2}$.

The expression for $\xi(q)$ that follows from quantum theory is of the form $\xi(q) \approx 2Bq^{-1}\langle E^{-1}\rangle \Xi_q \exp(-l^2 \times q^2/2)$ where Ξ_q [and Ξ in Eq. (6) below] allows for the filling of the excited Landau levels and $l = (\hbar/eB)^{1/2}$ is the magnetic length. In the limit of a quantizing field, $\hbar \omega_c/kT \gg 1$, $\Xi_q = \Xi = 1$. The reduced resistivity is then given by

$$\rho_{mq}^{*} = 0.15 (\omega_{c}/\omega_{p}) (\hbar \omega_{c}/kT)^{3/2} \Xi, \qquad (6)$$

which exactly coincides with Eq. (5) in the range $B \gg B_0$, $\hbar \omega_c / kT \ll 1$, where both the above classical and quantum theories apply.

We now compare this theory with three data sets [set 1: $n=0.6 \times 10^{12}$ cm⁻², T=1.003 K; set 2: $n=2.1 \times 10^{12}$ cm⁻², T = 1.003 K; set 3: $n = 2.1 \times 10^{12}$ cm⁻², T = 1.215K] in Figs. 1, 2, and 3 where the normalized resistivity is plotted versus B. At low fields (though $\mu_0 B > 1$ for all the data shown) the magnetoresistance is in qualitative and quantitative contradiction with the SCBA theory (lines a_1, a_2 , and a_3 , where the subscripts refer to the corresponding data sets). Figure 1 shows the calculations for the many-electron theories for data set 1. The low field classical theory, Eq. (3) (line b_1), predicts a small magnetoresistance for $\eta \ll 1$ which corresponds to $B \ll 0.2$ T. The onset field for magnetoresistance B_0 from the classical theory, Eq. (5), is 0.44 T for data set 1 (B_0 =0.69 and 0.76 T for data sets 2 and 3). But quantum effects are already important in this region as $\hbar \omega_c = kT$ at $B_q = 0.75$ T at 1 K. For B > 2 T we can use the quantum magnetoresistance ρ_{mq}^* , Eq. (6), shown by line c_1 . However, for $\rho^* > 5$, the results of the many-electron theory and of the single-electron SCBA differ by less than a factor of 2 and the combined total resistivity ρ_t is then calculated from the expression

$$\frac{1}{\rho_t} = \frac{1}{\rho_m} + \frac{\rho_t}{\rho_s^2} \,, \tag{7}$$

which is derived from the Einstein diffusion equation in which the scattering rate is proportional to $\hbar \omega_c/\Gamma$, where Γ is the energy uncertainty of each Landau level. Equation (7) incorporates the self-consistent nature of the SCBA. The normalized total resistivity ρ_t^* is plotted as line d_1 and shows good agreement with the measurements, particularly since there are no adjustable parameters in these calculations. Figure 2 demonstrates the density dependence of ρ^* at a fixed temperature where the SCBA result is independent of density while ρ_t^* increases as the density decreases as shown by lines d_1 and d_2 . Figure 3 demonstrates the temperature dependence of ρ^* at a fixed density compared to the SCBA results (lines a_2 and a_3) and ρ_t^* (lines d_1 and d_2).

At the highest fields the SCBA, and collision broadening of the Landau levels, will dominate the magnetoresistance. The crossover from many-electron kinetics to the independent electron approach of the SCBA occurs with increasing B and T since Eq. (2) only holds if the duration of a collision $\tau_c \ll \tau_B$, the relaxation time. For classically strong fields τ_c is equal to \hbar/kT for $\eta \ll 1$ and $\chi_T B/E$ for $\eta \gg 1$ and $\zeta > 1$, respectively, while for quantizing fields $\tau_c = lB/E \propto B^{1/2}$. But the scattering rate τ_B^{-1} increases rapidly at high B and T and the electron kinetics and scattering become essentially single electron in nature. At the crossover $\tau_B \approx \tau_c \sim (\tau_B)_{\text{SCBA}}$ [note that $(\tau_B)_{SCBA} \sim (\tau_B \tau_c)^{1/2}$ or $\rho \setminus O(*, mq) \approx \rho_{SCBA}^*$. In terms of the zero-field mobility μ_0 , the SCBA will apply in the quantum limit for fields $B \ge 5 \times 10^{-10} \mu_0^{1/2} T^{1/2} n^{3/4}$ T. In the experiments of Adams and Paalanen [8] and van der Heijden et al. [6] this condition was satisfied for B > 1 T.

In conclusion, we have observed and explained the many-electron character of the magnetoresistance of a

2DEG in classically strong and in quantizing magnetic fields. The crossover from many- to single-electron kinetics has been observed with increasing magnetic fields.

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